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## FDMC7582 N-Channel PowerTrench<sup>®</sup> MOSFET 25 V, 49 A, 5.0 m $\Omega$

## Features

- Max r<sub>DS(on)</sub> = 5.0 mΩ at V<sub>GS</sub> = 10 V, I<sub>D</sub> = 16.7 A
- Max  $r_{DS(on)}$  = 7.5 m $\Omega$  at V<sub>GS</sub> = 4.5 V, I<sub>D</sub> = 13.6 A
- State-of-the-art switching performance
- Lower output capacitance, gate resistance, and gate charge boost efficiency
- Shielded gate technology reduces switch node ringing and increases immunity to EMI and cross conduction
- Clip bonding technology further reduces On resistance and source inductance
- RoHS Compliant

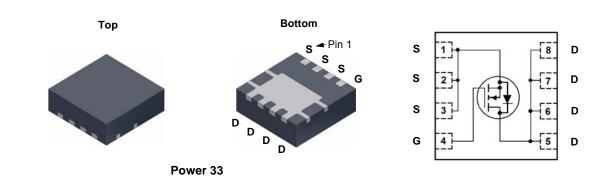


## **General Description**

This N-Channel MOSFET has been designed specifically to improve the overall efficiency and to minimize switch node ringing of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low rDS(on), fast switching speed and body diode reverse recovery performance..

## Application

- High side switching for high end computing
- High power density DC-DC synchronous buck
- Low loss load switch
- Communication & telecon Point of Load



## MOSFET Maximum Ratings T<sub>A</sub> = 25 °C unless otherwise noted

Symbol	Parameter			Ratings	Units	
V <sub>DS</sub>	Drain to Source Voltage			25	V	
V <sub>GS</sub>	Gate to Source Voltage		(Note 3)	±20	V	
	Drain Current - Continuous (Package limited) Tc=25C			49		
	- Continuous (Silicon Limited) Tc=25C			76	_	
ID	- Continuous	T <sub>A</sub> = 25 °C	(Note 1a)	16.7	— A	
	- Pulsed			60		
E <sub>AS</sub>	Single Pulse Avalanche Energy		(Note 4)	38	mJ	
P <sub>D</sub>	Power Dissipation	T <sub>C</sub> = 25 °C		52		
	Power Dissipation	T <sub>A</sub> = 25 °C	(Note 1a)	2.3		
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Ra	ange		-55 to +150	°C	

## **Thermal Characteristics**

$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case	2.4	°C/W
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	53	C/W

## Package Marking and Ordering Information

Dev	/ice Marking	Device	Package	Reel Size	Tape Width	Quantity
F	DMC7582	FDMC7582	Power 33	13 "	12 mm	3000 units

April 2012

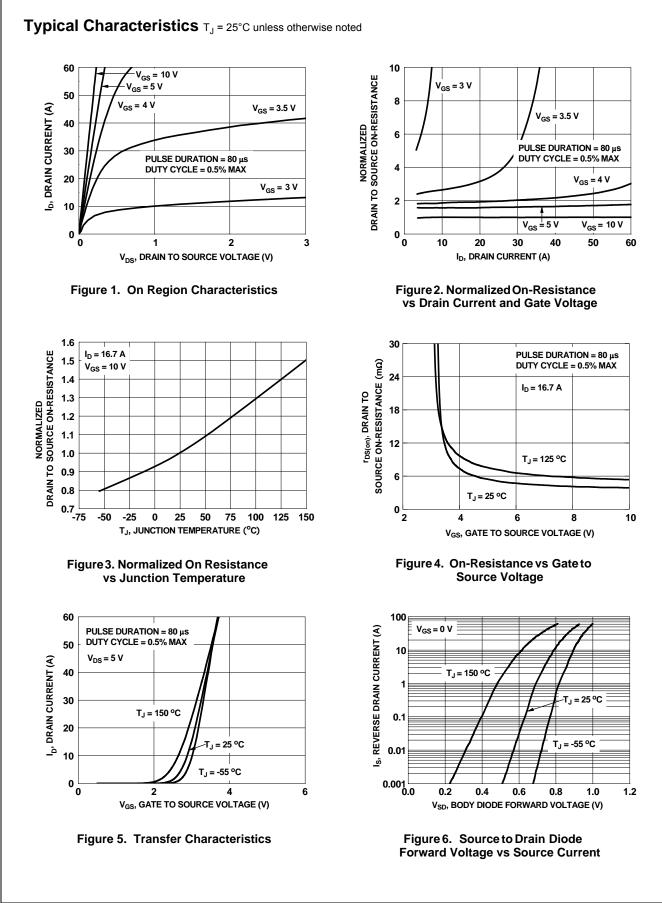
FDMC7582
N-Channel
<b>PowerTrench</b>
<sup>®</sup> MOSFET

eristics Drain to Source Breakdown Voltage			Тур	Max	Units
Drain to Source Breakdown Voltage				1	1
	I <sub>D</sub> = 250 μA , V <sub>GS</sub> = 0 V	25			V
Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}$ , referenced to 25 °C		19		mV/°C
Zero Gate Voltage Drain Current	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V			1	μA
Gate to Source Leakage Current, Forward				100	nA
eristics				1	1
	V <sub>CS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 µA	1.2	1.7	2.5	V
Gate to Source Threshold Voltage	$I_D = 250 \ \mu\text{A}$ , referenced to 25 °C		-5		mV/°C
•	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 16.7 A		4.0	5.0	
Static Drain to Source On Resistance	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 13.6 A		6.0	7.5	mΩ
	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 16.7 A,T <sub>J</sub> = 125 °C		5.4	7.0	
Forward Transconductance	V <sub>DD</sub> = 5 V, I <sub>D</sub> = 16.7 A		58		S
naracteristics					
nput Capacitance			1348	1795	pF
			372	495	pF
Reverse Transfer Capacitance	T = 1 MHZ		79	120	pF
Gate Resistance		0.1	0.9	2.9	Ω
Characteristics					
			8.8	18	ns
,	Vpp = 13 V lp = 16 7A				ns
				-	ns
					ns
					nC
					nC
_	– V <sub>DD</sub> = 13 V, I <sub>D</sub> = 16.7 A				nC
-	-				nC
			2.0		110
	$V_{cc} = 0 V I_c = 16.7 A$ (Note 2)		0.8	1.3	V
Source to Drain Diode Forward Voltage					
Reverse Recovery Time					ns
•	– I <sub>F</sub> = 16.7 A, di/dt = 100 A/μs		7	14	nC
	eristics Gate to Source Threshold Voltage Gate to Source Threshold Voltage Gate to Source Threshold Voltage Gemperature Coefficient  Static Drain to Source On Resistance Groward Transconductance  aracteristics  nput Capacitance Characteristics  Turn-On Delay Time Rise Time Turn-Off Delay Time Gate Charge at 10V Total Gate Charge Characteristics  Characteristics  Could Gate Charge Charge Characteristics  Characteristics  Could Gate Charge Charge Charge Characteristics  Characteristics  Charge Ch	eristicsSate to Source Threshold Voltage $V_{GS} = V_{DS}$ , $I_D = 250 \ \mu$ ASate to Source Threshold Voltage $I_D = 250 \ \mu$ A, referenced to 25 °CStatic Drain to Source On Resistance $V_{GS} = 10 \ V$ , $I_D = 16.7 \ A$ Static Drain to Source On Resistance $V_{GS} = 10 \ V$ , $I_D = 16.7 \ A$ Static Drain to Source On Resistance $V_{DD} = 5 \ V$ , $I_D = 16.7 \ A$ Static Drain to Source On Resistance $V_{DD} = 5 \ V$ , $I_D = 16.7 \ A$ Static Drain to Source On Resistance $V_{DD} = 5 \ V$ , $I_D = 16.7 \ A$ Static Capacitance $V_{DD} = 5 \ V$ , $I_D = 16.7 \ A$ Static Capacitance $V_{DS} = 13 \ V$ , $V_{GS} = 0 \ V$ , f = 1 MHzState Resistance $V_{DD} = 13 \ V$ , $I_D = 16.7 \ A$ , $V_{GS} = 10 \ V$ , $R_{GEN} = 6 \ \Omega$ Characteristics $V_{DD} = 13 \ V$ , $I_D = 16.7 \ A$ , $V_{GS} = 10 \ V$ , $R_{GEN} = 6 \ \Omega$ State Charge at 10V $V_{DD} = 13 \ V$ , $I_D = 16.7 \ A$ State Charge at 4.5V $V_{DD} = 13 \ V$ , $I_D = 16.7 \ A$ State Charge at 4.5V $V_{DD} = 13 \ V$ , $I_D = 16.7 \ A$ State to Drain "Miller" Charge $V_{DD} = 13 \ V$ , $I_D = 16.7 \ A$ State to Drain "Miller" Charge $V_{CS} = 0 \ V$ , $I_S = 16.7 \ A$ State to Drain "Miller" Charge $V_{GS} = 0 \ V$ , $I_S = 16.7 \ A$ State to Drain Diode Forward Voltage $V_{GS} = 0 \ V$ , $I_S = 2 \ A$ State to Drain Diode Forward Voltage $V_{GS} = 0 \ V$ , $I_S = 2 \ A$ State to Drain Diode Forward Voltage $V_{GS} = 0 \ V$ , $I_S = 2 \ A$ State to Drain Diode Forward Voltage $V_{GS} = 0 \ V$ , $I_S = 2 \ A$ State	eristicsSate to Source Threshold Voltage $V_{GS} = V_{DS}$ , $I_D = 250 \ \mu$ A1.2Sate to Source Threshold Voltage $I_D = 250 \ \mu$ A, referenced to 25 °C $I_D = 250 \ \mu$ A, referenced to 25 °CStatic Drain to Source On Resistance $V_{GS} = 10 \ V$ , $I_D = 16.7 \ A$ $V_{GS} = 10 \ V$ , $I_D = 16.7 \ A$ Static Drain to Source On Resistance $V_{GS} = 10 \ V$ , $I_D = 16.7 \ A$ $V_{GS} = 10 \ V$ , $I_D = 16.7 \ A$ Transconductance $V_{DD} = 5 \ V$ , $I_D = 16.7 \ A$ $V_{DD} = 5 \ V$ , $I_D = 16.7 \ A$ Static Capacitance $V_{DD} = 5 \ V$ , $I_D = 16.7 \ A$ $V_{CS} = 0 \ V$ , $f = 1 \ MHz$ Sate Resistance0.1 $Characteristics$ State Resistance0.1 $V_{DD} = 13 \ V$ , $I_D = 16.7 \ A$ , $V_{GS} = 0 \ V$ , $f = 1 \ MHz$ State Resistance0.1 $Characteristics$ State Resistance $V_{DD} = 13 \ V$ , $I_D = 16.7 \ A$ , $V_{GS} = 10 \ V$ , $R_{GEN} = 6 \ \Omega$ State Charge at 4.5V $V_{DD} = 13 \ V$ , $I_D = 16.7 \ A$ State Charge at 4.5V $V_{DD} = 13 \ V$ , $I_D = 16.7 \ A$ State Charge at 4.5V $V_{DD} = 13 \ V$ , $I_D = 16.7 \ A$ State to Drain "Miller" Charge $V_{CS} = 0 \ V$ , $I_S = 16.7 \ A$ State to Drain "Miller" Charge $V_{GS} = 0 \ V$ , $I_S = 16.7 \ A$ State to Drain Diode Forward Voltage $V_{GS} = 0 \ V$ , $I_S = 2 \ A$ Reverse Recovery Time $I_C = 16.7 \ A$ State Resource to Drain Diode Forward Voltage $V_{GS} = 0 \ V$ , $I_S = 2 \ A$ State to Drain Diode Forward Voltage $V_{GS} = 0 \ V$ , $I_S = 2 \ A$ State to Drain Diode Forward Voltage $V_{GS} = $	eristicsSate to Source Threshold Voltage $V_{GS} = V_{DS}$ , $I_D = 250 \ \mu$ A1.21.7Sate to Source Threshold Voltage $I_D = 250 \ \mu$ A, referenced to 25 °C-5emperature Coefficient $V_{GS} = 10 \ V$ , $I_D = 16.7 \ A$ 4.0Vaste to Drain to Source On Resistance $V_{GS} = 10 \ V$ , $I_D = 16.7 \ A$ 4.0Vaste to Drain to Source On Resistance $V_{GS} = 10 \ V$ , $I_D = 16.7 \ A$ 58maracteristics $V_{DD} = 5 \ V$ , $I_D = 16.7 \ A$ 58maracteristics $V_{DD} = 5 \ V$ , $I_D = 16.7 \ A$ 58maracteristics $V_{DS} = 13 \ V$ , $V_{GS} = 0 \ V$ , f = 1 MHz1348Dutput Capacitance $V_{DS} = 13 \ V$ , $V_{GS} = 0 \ V$ , f = 1 MHz79Sate Resistance0.10.9Characteristics $V_{DD} = 13 \ V$ , $I_D = 16.7 \ A$ , $V_{CS} = 10 \ V$ , $R_{GEN} = 6 \ \Omega$ State Time $V_{DS} = 13 \ V$ , $I_D = 16.7 \ A$ , $V_{CS} = 10 \ V$ , $R_{GEN} = 6 \ \Omega$ State Resistance $V_{DD} = 13 \ V$ , $I_D = 16.7 \ A$ , $V_{DD} = 13 \ V$ , $I_D = 16.7 \ A$ State Time $V_{DD} = 13 \ V$ , $I_D = 16.7 \ A$ , $V_{DD} = 13 \ V$ , $I_D = 16.7 \ A$ State Torn-Off Delay Time $V_{DD} = 13 \ V$ , $I_D = 16.7 \ A$ State to Drain "Miller" Charge $V_{DD} = 13 \ V$ , $I_D = 16.7 \ A$ State to Drain "Miller" Charge $V_{CS} = 0 \ V$ , $I_S = 16.7 \ A$ State to Drain Diode Forward Voltage $V_{GS} = 0 \ V$ , $I_S = 16.7 \ A$ Reverse Recovery Time $V_{CS} = 0 \ V$ , $I_S = 2 \ A$ In = 16 7 \ A $V_{CS} = 0 \ V$ , $I_S = 2 \ A$ State to Drain Diode Forw	eristics         V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 µA         1.2         1.7         2.5           Sate to Source Threshold Voltage emperature Coefficient         I <sub>D</sub> = 250 µA, referenced to 25 °C         -5         -5           V <sub>GS</sub> = 10 V, I <sub>D</sub> = 16.7 A         4.0         5.0           V <sub>GS</sub> = 10 V, I <sub>D</sub> = 16.7 A         4.0         5.0           V <sub>GS</sub> = 10 V, I <sub>D</sub> = 16.7 A         4.0         5.0           V <sub>GS</sub> = 10 V, I <sub>D</sub> = 16.7 A         4.0         5.0           V <sub>GS</sub> = 10 V, I <sub>D</sub> = 16.7 A         4.0         5.0           V <sub>GS</sub> = 10 V, I <sub>D</sub> = 16.7 A         4.0         5.0           varacteristics         V <sub>DS</sub> = 13.0 V, I <sub>D</sub> = 16.7 A         58           naracteristics         1.12         1.12         1.12           Num-On Delay Time         V <sub>DS</sub> = 13 V, V <sub>GS</sub> = 0 V, f = 1 MHz         1348         1795           Characteristics         0.1         0.9         2.9           Characteristics         0.1         0.9         2.9           Characteristics         V <sub>DD</sub> = 13 V, I <sub>D</sub> = 16.7 A, V <sub>GS</sub> = 6 Ω         20         36           Time Of Delay Time         V <sub>DD</sub> = 13 V, I <sub>D</sub> = 16.7 A         20         28           Otal Gate Charge at 10V         V <sub>DD</sub> = 13 V, I <sub>D</sub> = 16.7 A         3.9         2.5

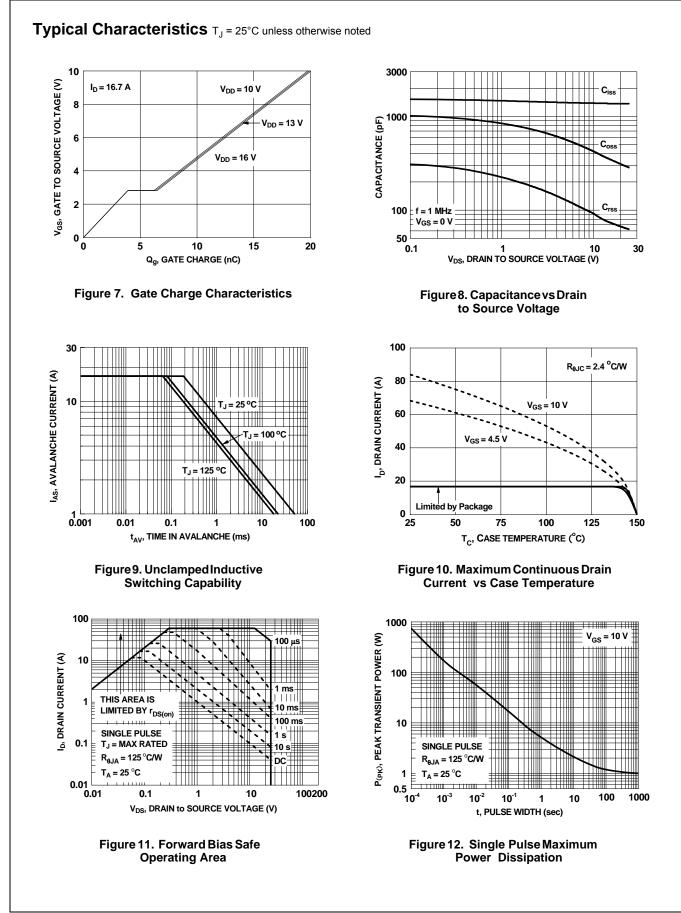
2. Pulse Test: Pulse Width < 300  $\mu s,$  Duty cycle < 2.0%.

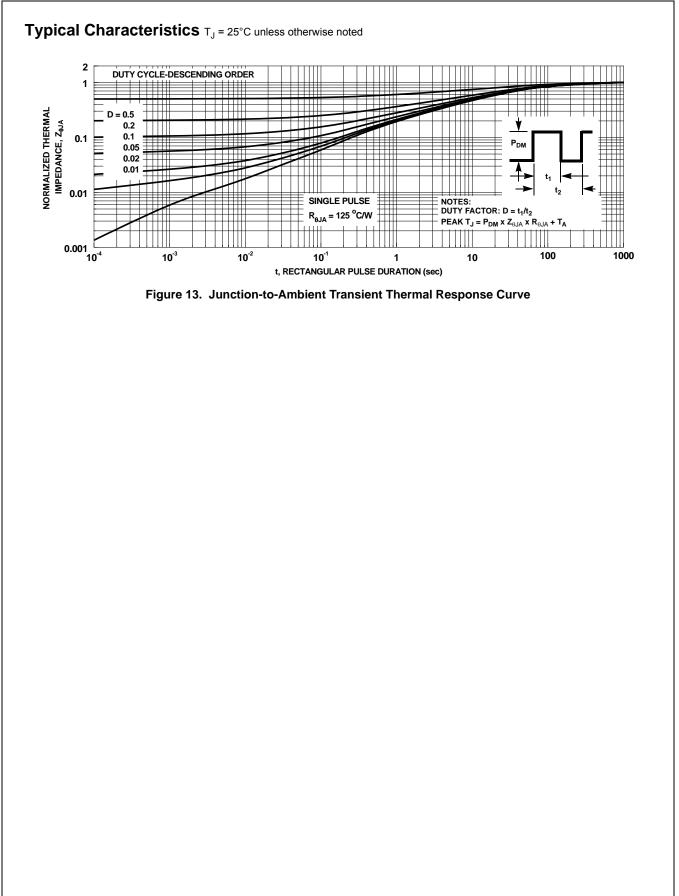
3. As an N-ch device, the negative Vgs rating is for low duty cycle pulse ocurrence only. No continuous rating is implied.

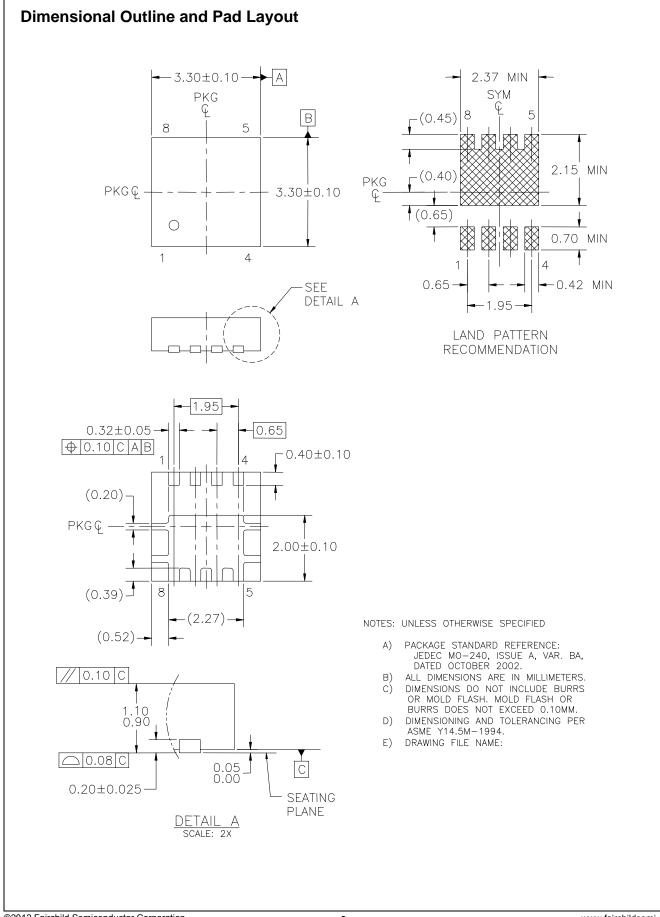
4. Eas of 38 mJ is based on starting TJ = 25  $_{\circ}$ C; N-ch: L = 0.3 mH, Ias = 16 A, VDD = 23 V, VGs = 10 V.











FDMC7582 N-Channel PowerTrench<sup>®</sup> MOSFET



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